

# RJK6018DPK

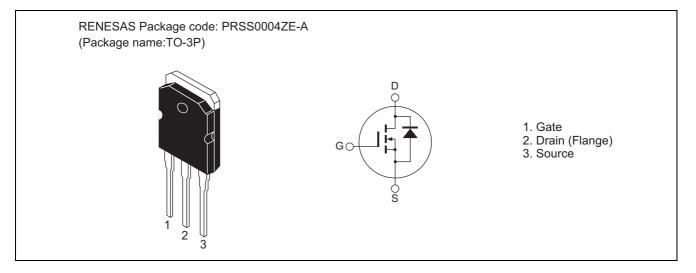
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1537-0100 Rev.1.00 Apr 04, 2007

# Features

- Low on-resistance
- Low leakage current
- High speed switching

# Outline



# **Absolute Maximum Ratings**

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	600	V
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	I <sub>D</sub>	30	А
Drain peak current	Note1	90	А
Body-drain diode reverse drain current	I <sub>DR</sub>	30	А
Body-drain diode reverse drain peak current	Note1 I <sub>DR (pulse)</sub>	90	А
Avalanche current	I <sub>AP</sub> <sup>Note3</sup>	6	А
Avalanche energy	E <sub>AR</sub> <sup>Note3</sup>	1.9	mJ
Channel dissipation	Pch <sup>Note2</sup>	200	W
Channel to case thermal impedance	θch-c	0.625	°C/W
Channel temperature	Tch	150	۵°
Storage temperature	Tstg	-55 to +150	۵°

Notes: 1.  $PW \le 10 \ \mu s$ , duty cycle  $\le 1\%$ 

2. Value at Tc = 25°C

3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C

# **Electrical Characteristics**

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Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	600		—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>		_	1	μΑ	$V_{DS} = 600 \text{ V}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±0.1	μΑ	$V_{GS} = \pm 30$ V, $V_{DS} = 0$
Gate to source cutoff voltage	V <sub>GS(off)</sub>	3.0	_	4.5	V	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R <sub>DS(on)</sub>	_	0.200	0.235	Ω	$I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	4100	_	pF	V <sub>DS</sub> = 25 V
Output capacitance	Coss	_	380	_	pF	V <sub>GS</sub> = 0 f = 1 MHz
Reverse transfer capacitance	Crss	_	37	_	pF	
Turn-on delay time	t <sub>d(on)</sub>	_	50	—	ns	I <sub>D</sub> = 15 A
Rise time	tr	_	88		ns	$V_{GS} = 10 V$ $R_L = 20 \Omega$ $Rg = 10 \Omega$
Turn-off delay time	t <sub>d(off)</sub>	_	140		ns	
Fall time	t <sub>f</sub>	_	81		ns	
Total gate charge	Qg		92		nC	V <sub>DD</sub> = 480 V
Gate to source charge	Qgs		22		nC	V <sub>GS</sub> = 10 V I <sub>D</sub> = 30 A
Gate to drain charge	Qgd		38	_	nC	
Body-drain diode forward voltage	V <sub>DF</sub>	_	0.90	1.50	V	$I_F = 30 \text{ A}, V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	480	—	ns	$I_F = 30 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu \text{s}$

Notes: 4. Pulse test

# Package Dimensions

Package Name TO-3P	JEITA Package Code SC-65	RENESAS Code	Previous Code	MASS[Typ.]	
10-3P	SC-65	PRSS0004ZE-A 15.6 ± 0.3	TO-3P/TO-3PV	5.0g 4.8 ± 0.2 1.5 2.8 0.6 ± 0.2	Unit: mm
	<u>5.45 ± 0</u>		<u>.0</u> <u>.0</u> <u>.5.45 ± 0.5</u>		

# **Ordering Information**

Part No.	Quantity	Shipping Container
RJK6018DPK-00	360 pcs	Box (Tube)

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